



NCE N-Channel Enhancement Mode Power MOSFET

Description

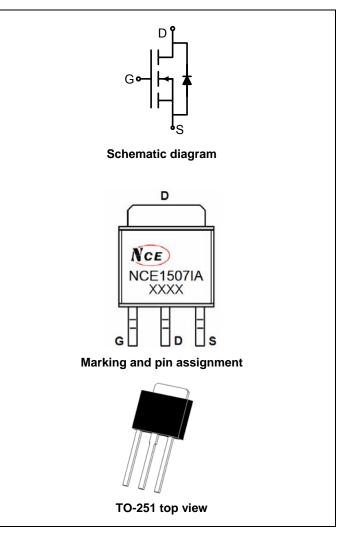
The NCE1507IA uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- V_{DS} = 150V, I_D = 7A $R_{DS(ON)}$ < 290mΩ @ V_{GS} =10V (Typ:255mΩ)
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and high frequency circuits



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity	
NCE1507IA	NCE1507IA	TO-251	-	-	-	

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	150	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	7	Α
Drain Current-Pulsed (Note 1)	I _{DM}	50	А
Maximum Power Dissipation	P _D	30	W
Operating Junction and Storage Temperature Range	T_J, T_STG	-55 To 175	℃

Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	$R_{ heta JC}$	5	°C/W



Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	150	-	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =150V,V _{GS} =0V	-	-	1	μA	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	1.5	2	2.5	V	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =5A	-	255	290	mΩ	
Forward Transconductance	g FS	V _{DS} =15V,I _D =1.5A	-	3	-	S	
Dynamic Characteristics (Note4)			•				
Input Capacitance	C _{lss}	\/ -25\/\/ -0\/	-	235	-	PF	
Output Capacitance	C _{oss}	V_{DS} =25V, V_{GS} =0V, F=1.0MHz	-	36	-	PF	
Reverse Transfer Capacitance	C _{rss}	F=1.UIVITZ	-	20	-	PF	
Switching Characteristics (Note 4)							
Turn-on Delay Time	t _{d(on)}		-	8	-	nS	
Turn-on Rise Time	t _r	V_{DD} =75 V , I_D =1 A , R_L =75 Ω	-	10	-	nS	
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =6 Ω	-	20	-	nS	
Turn-Off Fall Time	t _f		-	15	-	nS	
Total Gate Charge	Qg	\/ -75\/ -4.50	-	8		nC	
Gate-Source Charge	Q _{gs}	$V_{DS}=75V,I_{D}=1.5A,$ $V_{GS}=10V$	-	1.4	-	nC	
Gate-Drain Charge	Q_{gd}	VGS-1UV	-	2.1	-	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =2A	-	-	1.2	V	
Diode Forward Current (Note 2)	Is		-	-	7	Α	

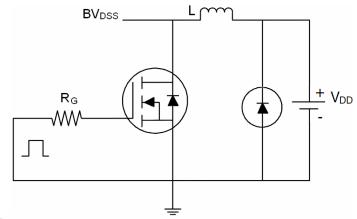


Notes:

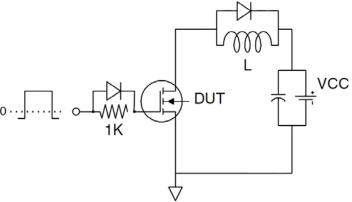
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to product

Test Circuit

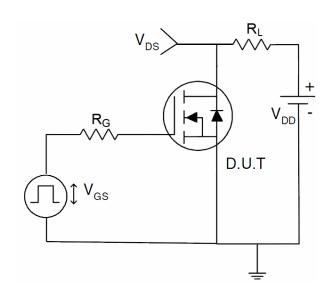
1) E_{AS} Test Circuit



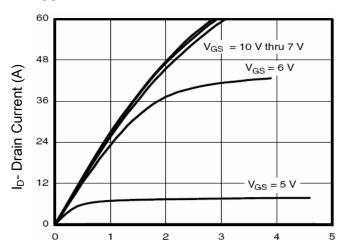
2) Gate Charge Test Circuit



3) Switch Time Test Circuit

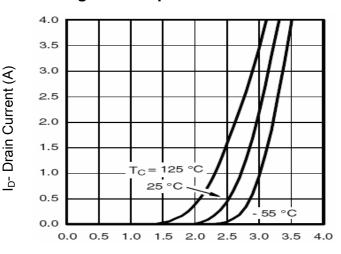


Typical Electrical and Thermal Characteristics (Curves)



Vds Drain-Source Voltage (V)

Figure 1 Output Characteristics



Vgs Gate-Source Voltage (V)

Figure 2 Transfer Characteristics

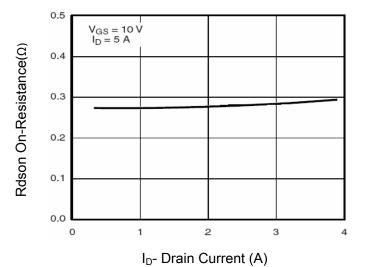


Figure 3 Rdson- Drain Current

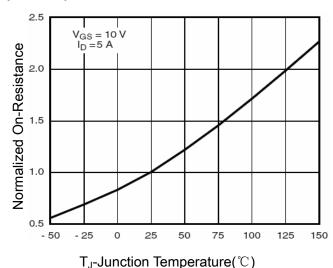
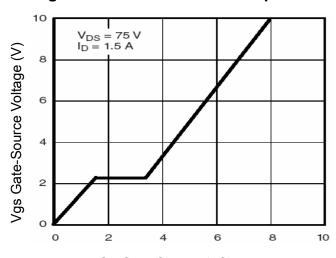


Figure 4 Rdson- Junction Temperature



Qg Gate Charge (nC)

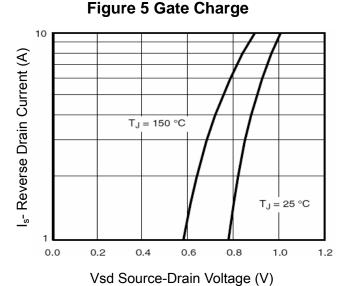


Figure 6 Source- Drain Diode Forward

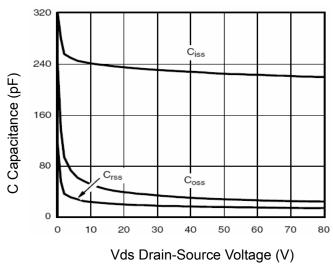
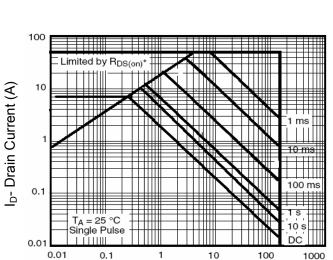


Figure 7 Capacitance vs Vds



Vds Drain-Source Voltage (V)

Figure 8 Safe Operation Area

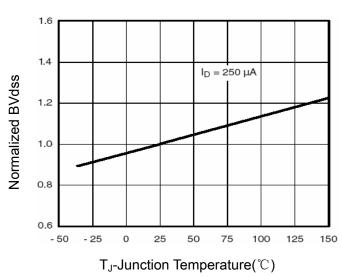
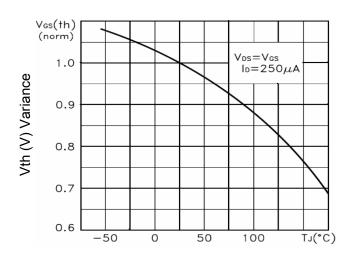


Figure 9 BV_{DSS} vs Junction Temperature



T_J-Junction Temperature(°C)

Figure 10 V_{GS(th)} vs Junction Temperature

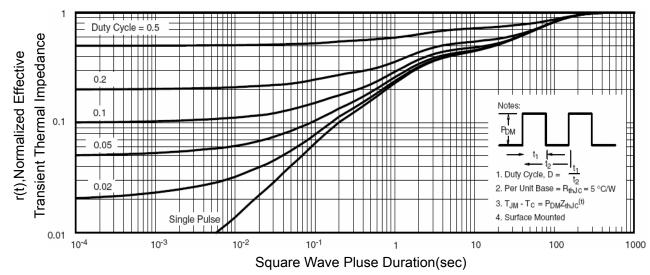
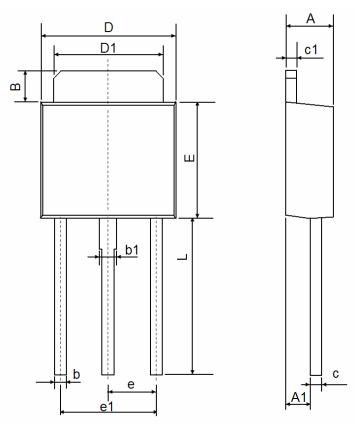


Figure 11 Normalized Maximum Transient Thermal Impedance



TO-251 Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	2.200	2.400	0.087	0.094	
A1	1.050	1.350	0.042	0.054	
В	1.350	1.650	0.053	0.065	
b	0.500	0.700	0.020	0.028	
b1	0.700	0.900	0.028	0.035	
С	0.430	0.580	0.017	0.023	
c1	0.430	0.580	0.017	0.023	
D	6.350	6.650	0.250	0.262	
D1	5.200	5.400	0.205	0.213	
E	5.400	5.700	0.213	0.224	
е	2.300 TYP		0.091 TYP		
e1	4.500	4.700	0.177	0.185	
L	7.500	7.900	0.295	0.311	

Notes

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- $5. \ Controlling \ dimension \ is \ millimeter, \ converted \ inch \ dimensions \ are \ not \ necessarily \ exact.$

Pb-Free Product

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